Improved effective equation for the Rashba spin-orbit coupling in semiconductor nanowires

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Presentation Rashba SOC Motivation

Reference – Samuel D. Escribano, Alfredo Levy Yeyati and Elsa Prada, *Improved effective equation for the Rashba spin-orbit coupling in semiconductor nanowires*, arXiv:2001.04375 (2020).

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 $H_{SO} = \vec{\alpha} \cdot \left(\vec{k} \times \vec{\sigma} \right)$

Presentation Rashba SOC Motivation

$$H_{SO} = \vec{\alpha} \cdot \left(\vec{k} \times \vec{\sigma}
ight) \longrightarrow {}^{\text{The SOC}}_{\text{spatial s}}$$

SOC $ec{lpha}$ is the result of a tial symmetry breaking $ec{lpha}$

$$\vec{\alpha} \sim \vec{\nabla}\phi$$
$$\vec{\alpha} = \vec{\alpha}_D + \vec{\alpha}_R$$

Presentation Rashba SOC Motivation



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 $H_{SO} = \vec{\alpha} \cdot \left(\vec{k} \times \vec{\sigma}\right) \longrightarrow \text{The SOC } \vec{\alpha} \text{ is the result of a } \vec{\alpha} \sim \vec{\nabla}\phi$ spatial symmetry breaking $\vec{\alpha} = \vec{\alpha}_D + \vec{\alpha}_R$

Dresselhaus SOC

 $\vec{\alpha}_D$ is the result of a bulk inversion asymmetry

The unit cell itself is not symmetric

Rashba SOC

 $\vec{\alpha}_R$ is the result of a structural inversion asymmetry

Interfaces and the electrostatic surrounding break the symmetry



R. Winkler et al., Spin-Orbit Coupling in Two-Dimensional Electron and Hole Systems, Vol. 41 (Springer, 2003).

Presentation Rashba SOC **Motivation**



A. Manchon et al. Nat. Mat. 14, 871 (2015).

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These are based on InAs, InSb or GaAs nanowires

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The precise value of the SOC is crucial in all these systems!!!

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The precise value of the SOC is crucial in all these systems!!!

We look for a simple equation which describes the Rashba SOC in this kind of nanowires

Description of the Rashba SOC in several works:

- Rough constant extracted from experiments.
- Extracted from numerical calculations of effective multiband k·p Hamiltonians.
 R. Winkler et al., Spin-Orbit Coupling in Two-Dimensional Electron and Hole Systems, Vol. 41 (Springer, 2003).
 T. Campos et al. PRB 97, 245402 (2018).
- Simplified effective equation extracted from Simplified multiband k·p Hamiltonians.
- Improved effective equation extracted from simplified multiband k·p Hamiltonians.
 Our work
 S. D. Escribano et al., arXiv:2001.04375

8-band k·p model Conduction band approximation Improved equation

Multiband $k \cdot p$ models are known to successfully reproduce the energy-band structure of III-V compound semiconductors. Because the SO coupling can be directly extracted from the shape of the energy spectrum, they are a reliable source of information about the SOC.

$$\begin{array}{l} \text{Basis} \longrightarrow |c \uparrow\rangle \quad |c \downarrow\rangle \quad |hh \uparrow\rangle \quad |hh \downarrow\rangle \quad |hh \downarrow\rangle \quad |hh \downarrow\rangle \quad |so \uparrow\rangle \quad |so \downarrow\rangle \\ = \begin{pmatrix} T_{c} & 0 & \frac{1}{\sqrt{6}}P_{k_{+}} & 0 & \frac{1}{\sqrt{2}}P_{k_{-}} & -\sqrt{\frac{2}{3}}P_{k_{z}} & \frac{1}{\sqrt{3}}P_{k_{z}} & \frac{1}{\sqrt{3}}P_{k_{z}} \\ 0 & T_{c} & -\sqrt{\frac{2}{3}}P_{k_{z}} & -\frac{1}{\sqrt{2}}P_{k_{+}} & 0 & -\frac{1}{\sqrt{6}}P_{k_{-}} & \frac{1}{\sqrt{3}}P_{k_{z}} & \frac{1}{\sqrt{3}}P_{k_{z}} \\ \frac{1}{\sqrt{6}}P_{k_{-}} & -\sqrt{\frac{2}{3}}P_{k_{z}} & T_{lh} & -\Omega^{\frac{1}{2}} & \Omega_{1} & 0 & \sqrt{\frac{3}{2}}\Omega_{2} & -\sqrt{2}\Omega_{3} \\ 0 & -\frac{1}{\sqrt{2}}P_{k_{-}} & -\Omega_{2} & T_{hh} & 0 & \Omega_{1} & -\sqrt{2}\Omega^{\frac{1}{1}} & \frac{1}{\sqrt{2}}\Omega_{2} \\ \frac{1}{\sqrt{2}}P_{k_{+}} & 0 & \Omega^{\frac{1}{1}} & 0 & T_{hh} & \Omega^{\frac{1}{2}} & \frac{1}{\sqrt{2}}\Omega^{\frac{1}{2}} & \sqrt{2}\Omega^{\frac{1}{1}} & \frac{1}{\sqrt{2}}\Omega_{2} \\ -\sqrt{\frac{2}{3}}P_{k_{z}} & -\frac{1}{\sqrt{6}}P_{k_{+}} & 0 & \Omega^{\frac{1}{1}} & \Omega_{2} & T_{lh} & \sqrt{2}\Omega_{3} & \sqrt{\frac{3}{2}}\Omega^{\frac{1}{2}} \\ -\frac{1}{\sqrt{3}}P_{k_{z}} & \frac{1}{\sqrt{3}}P_{k_{z}} & -\sqrt{2}\Omega_{3} & \frac{1}{\sqrt{2}}\Omega^{\frac{1}{2}} & \sqrt{2}\Omega_{1} & \sqrt{\frac{2}{3}}\Omega_{2} & 0 & T_{soff} \end{pmatrix} \end{array} \right)$$

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$$\text{Basis} \rightarrow |c\uparrow\rangle \quad |c\downarrow\rangle \quad |hh\uparrow\rangle \quad |hh\downarrow\rangle \quad |hh\downarrow\rangle \quad |so\uparrow\rangle \quad |so\downarrow\rangle \\ = \begin{pmatrix} T_c & 0 & \frac{1}{\sqrt{6}}Pk_+ & 0 & \frac{1}{\sqrt{2}}Pk_- & -\sqrt{\frac{2}{3}}Pk_z & \frac{1}{\sqrt{3}}Pk_z & \frac{1}{\sqrt{3}}Pk_+ \\ 0 & T_c & -\sqrt{\frac{2}{3}}Pk_z & -\frac{1}{\sqrt{2}}Pk_+ & 0 & -\frac{1}{\sqrt{6}}Pk_- & \frac{1}{\sqrt{3}}Pk_z & \frac{1}{\sqrt{3}}Pk_z \\ \frac{1}{\sqrt{6}}Pk_- & -\sqrt{\frac{2}{3}}Pk_z & T_{\text{lh}} & -\Omega^{\frac{1}{2}} & \Omega_1 & 0 & \sqrt{\frac{3}{2}}\Omega_2 & -\sqrt{2}\Omega_3 \\ 0 & -\frac{1}{\sqrt{2}}Pk_- & \Omega_2 & T_{\text{hh}} & 0 & \Omega_1 & -\sqrt{2}\Omega_1^{\frac{1}{2}} & \frac{1}{\sqrt{2}}\Omega_2^{\frac{1}{2}} & \sqrt{2}\Omega_1 \\ -\sqrt{\frac{2}{3}}Pk_z & -\frac{1}{\sqrt{6}}Pk_+ & 0 & \Omega_1^{\frac{1}{1}} & \Omega_2 & T_{\text{lh}} & \sqrt{2}\Omega_3 & \sqrt{\frac{3}{2}}\Omega_2^{\frac{1}{2}} \\ -\frac{1}{\sqrt{3}}Pk_z & \frac{1}{\sqrt{3}}Pk_z & -\sqrt{2}\Omega_3 & \frac{1}{\sqrt{2}}\Omega_2^{\frac{1}{2}} & \sqrt{2}\Omega_1 & \frac{1}{\sqrt{2}}\Omega_2 & \sqrt{2}\Omega_3 & T_{\text{soff}} & 0 \\ \frac{1}{\sqrt{3}}Pk_- & \frac{1}{\sqrt{3}}Pk_z & -\sqrt{2}\Omega_3 & \frac{1}{\sqrt{2}}\Omega_2^{\frac{1}{2}} & \sqrt{2}\Omega_1 & \sqrt{\frac{2}{3}}\Omega_2 & 0 & T_{\text{soff}} \end{pmatrix} \\ E_{\pm}^{(j)}(k_z) = \frac{\hbar^2k_z^2}{2m_{\text{eff}}^{(j)}} + E^{(j)} \pm \sqrt{(\alpha_{\text{eff}}^{(j)}k_z)^2 + (\beta_{\text{eff}}^{(j)}k_z^2)^2} \quad The SOC is extracted from the shape of the energy bands using an effective equation the shape of the energy bands using an effective equation the ene$$

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Results for the conduction band of an InAs nanowire embedded in an electrostatic environment:





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For low-dimensional materials, these multiband Hamiltonians are **computationally expensive**. They also have some further limitations.

8-band k·p model **Conduction band approximation** Improved equation

To overcome this problem, one would like to find an effective analytical equation for a Hamiltonian which only involves the conduction band. In order to obtain this Hamiltonian:

	H_{c}			H_{cv}		$H_{\rm c}$	v			
(, T _c	0	$\frac{1}{\sqrt{6}}Pk_+$	0	$\frac{1}{\sqrt{2}}Pk_{-}$	$-\sqrt{\frac{2}{3}}Pk_z$	$-\frac{1}{\sqrt{3}}Pk_z$	$\frac{1}{\sqrt{3}}Pk_+$		Perform a folding-down:
H =	$\frac{1}{\sqrt{6}}Pk_{-}$	$T_{\rm c}$ $-\sqrt{\frac{2}{3}Pk_{z}}$	$\frac{-\sqrt{\frac{2}{3}}Pk_z}{T_{\rm lh}}$	$\frac{-\frac{1}{\sqrt{2}}Pk_+}{-\Omega_2^{\dagger}}$	0 Ω_1	$\frac{-\frac{1}{\sqrt{6}}Pk_{-}}{0}$	$\frac{\frac{1}{\sqrt{3}}Pk_{-}}{\sqrt{\frac{3}{2}}\Omega_{2}}$	$\frac{\frac{1}{\sqrt{3}}Pk_z}{-\sqrt{2}\Omega_3}$		$H_{\rm CB} = H_{\rm c} + H_{\rm cv} G_{\rm v} H_{\rm cv}^{\dagger}$
	0 $\frac{1}{2}Pk_{\perp}$	$-\frac{1}{\sqrt{2}}Pk_{-}$	$-\Omega_2$ Ω_1^{\dagger}	$T_{\rm hh}$	0 The	$\Omega_1 \ \Omega_2^\dagger$	$\frac{\sqrt{2}}{-\sqrt{2}\Omega_1^{\dagger}}$ $\frac{1}{-\Omega_2^{\dagger}}$	$\frac{1}{\sqrt{2}}\Omega_2$ $\sqrt{2}\Omega_1^{\dagger}$		
	$-\sqrt{\frac{2}{3}}Pk_z$	$-\frac{1}{\sqrt{6}}Pk_+$		Ω_1^\dagger	Ω_2	$T_{ m lh}$	$\frac{\sqrt{2}^{2}\Omega_{2}}{\sqrt{2}\Omega_{3}}$	$\sqrt{\frac{3}{2}}\Omega_2^{\dagger}$		$\subseteq G_{\rm v} = (E - H_{\rm v})^{-1}$
	$-\frac{1}{\sqrt{3}}Pk_z$ $-\frac{1}{2}Pk_z$	$\frac{1}{\sqrt{3}}Pk_+$ $\frac{1}{\sqrt{3}}Pk_+$	$\sqrt{\frac{3}{2}\Omega_2^{\dagger}}$	$-\sqrt{2}\Omega_1$ $-\frac{1}{\Omega^{\dagger}}$	$\frac{1}{\sqrt{2}}\Omega_2$	$\sqrt{2}\Omega_3$	$T_{\rm soff}$	0 7		

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$$H_{c} \qquad H_{v} \qquad H_{v} \qquad H_{v} \qquad H_{v} \qquad Perform a folding-down: \\ H = \begin{pmatrix} T_{c} & 0 \\ 0 & T_{c} \\ \frac{1}{\sqrt{6}}Pk_{-} & -\sqrt{\frac{2}{3}}Pk_{z} \\ \frac{1}{\sqrt{6}}Pk_{-} & -\sqrt{\frac{2}{3}}Pk_{z} \\ -\sqrt{\frac{2}{3}}Pk_{z} & -\frac{1}{\sqrt{2}}Pk_{+} \\ 0 & -\frac{1}{\sqrt{2}}Pk_{+} \\ \frac{1}{\sqrt{2}}Pk_{-} & 0 \\ \sqrt{\frac{2}{3}}Pk_{z} & -\frac{1}{\sqrt{6}}Pk_{+} \\ \frac{1}{\sqrt{2}}Pk_{-} & \frac{1}{\sqrt{6}}Pk_{+} \\ \frac{1}{\sqrt{2}}Pk_{-} & \frac{1}{\sqrt{3}}Pk_{z} \\ \frac{1}{\sqrt{2}}Pk_{-} & \frac{1}{\sqrt{3}}Pk_{z} \\ \frac{1}{\sqrt{2}}Pk_{-} & \frac{1}{\sqrt{3}}Pk_{z} \\ \frac{1}{\sqrt{2}}Pk_{-} & \frac{1}{\sqrt{3}}Pk_{z} \\ \frac{1}{\sqrt{2}}Qk_{-} & -\sqrt{2}\Omega_{1} \\ \frac{1}{\sqrt{2}}\Omega_{2} & 0 \\ -\sqrt{2}\Omega_{3} & \frac{1}{\sqrt{2}}\Omega_{1}^{2} \\ \frac{1}{\sqrt{2}}\Omega_{2} & \sqrt{2}\Omega_{1} \\ \frac{1}{\sqrt{2}}\Omega_{2} & \sqrt{2}\Omega_{1} \\ \frac{1}{\sqrt{2}}\Omega_{2} & \frac{1}{\sqrt{2}}\Omega_{2} \\ \frac{1}{\sqrt{2}}\Omega_{2} & \frac{1}{\sqrt{2}}\Omega_{1} \\ \frac{1}{\sqrt{2}}\Omega_{1} & \frac{1}{\sqrt{2}}\Omega_{2} \\ \frac{1}{\sqrt{2}}\Omega_{2} & \frac{1}{\sqrt{2}}\Omega_{1} \\ \frac{1}{\sqrt{2}}\Omega_{2} \\ \frac{1}{\sqrt{2}}\Omega_{1} & \frac{1}{\sqrt{2}}\Omega_{2} \\ \frac$$

But one can expand $G_{
m v}$ in Dyson series assuming there is a small parameter.

8-band k·p model **Conduction band approximation** Improved equation

$$\frown \Omega_i \sim \gamma_i \frac{\hbar^2 k^2}{2m_0} \ll \Delta_{\rm g}, \Delta_{\rm soff}, P \longrightarrow G_{\rm v} = G_{\rm v}^{(0)} + G_{\rm v}^{(0)} V G_{\rm v}^{(0)} + \dots$$
 Intra-valence band couplings

8-band k·p model **Conduction band approximation** Improved equation



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Results for the conduction band of an InAs nanowire embedded in an electrostatic environment:





8-band k·p model **Conduction band approximation** Improved equation

Results for the conduction band of an InAs nanowire embedded in an electrostatic environment:





This analytical equation for the SOC fails predicting the numerical behaviour, precisely because the intra-valence band interactions have been neglected. $k\sim$

W

8-band k·p model Conduction band approximation Improved equation

Because confinement effects become relevant, one has to *improve* the description of the Rashba SOC to include them:

8-band k·p model Conduction band approximation Improved equation

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Option 1: one could go beyond zeroth order in Dyson series.
 All terms must be included Hard task

Because confinement effects become relevant, one has to *improve* the description of the Rashba SOC to include them:

- Option 1: one could go beyond zeroth order in Dyson series.
 All terms must be included
 Hard task
- Option 2: one may find an heuristic equation which reproduces the results of the 8-band model. We propose to use the same zeroth-order SOC equation, but substituting the Kane parameter *P*, by another one *P*_{fit}, chosen so that it reproduces the 8-band model calculations. To this end, we fit this equation to that calculations.

We call to this equation, **improved** SOC
$$\vec{\alpha}_R(\vec{r}) \simeq \frac{P_{\rm fit}^2}{3} \vec{\nabla} \left(\frac{1}{E_h - E^{(j)} - e\phi(\vec{r})} - \frac{1}{E_{\rm soff} - E^{(j)} - e\phi(\vec{r})} \right)$$
$$\vec{E} = E^{(j)} + E(k_z)$$

$P_{\rm fit}$	Zinc-blende (111)	Wurtzite (0001)
InAs	1252 ± 12	$723.0{\pm}0.1$
InSb	1082 ± 7	-
GaAs	1912 ± 18	-
GaSb	1657 ± 35	-

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The improved equation predicts correctly the behaviour of the more sophisticated 8-band model with **just one fitting parameter**.

8-band k·p model Conduction band approximation Improved equation

We show that P_{fit} :

- Is (roughly) independent of the subband, at least for the lowest ones.
- Is (roughly) independent of the electrostatic environment and the electric field.
- Depends on the width of the nanowire, although slightly for a certain range (i.e. [50,200]nm).



Comparison to experiments

We compare the results provided by the improved equation with data extracted from different magneto-transport experiments. We find an excellent agreement.



Take-home message

If you want to describe accurately the SOC in nanowires use the improved equation

$$\vec{\alpha}_R(\vec{r}) \simeq \frac{P_{\text{fit}}^2}{3} \vec{\nabla} \left(\frac{1}{E_h - E^{(j)} - e\phi(\vec{r})} - \frac{1}{E_{\text{soff}} - E^{(j)} - e\phi(\vec{r})} \right)$$

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For further details, see: **arXiv:2001.04375** For any question or inquire, don't hesitate to contact me: **samuel.diaz@uam.es**

